





### 100V PNP MEDIUM POWER TRANSISTOR IN SOT223

### **Features**

- BV<sub>CEO</sub> > -100V
- I<sub>C</sub> = -1A High Continuous Current
- I<sub>CM</sub> = -2A Peak Pulse Current
- Low Saturation Voltage
- Complementary NPN Type: FZT493
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

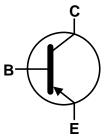
### **Mechanical Data**

- Case: SOT223
- Case material: Molded Plastic. "Green" Molding Compound;
  UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

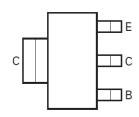




Top View



Device Symbol



Top View Pin-Out

### **Ordering Information** (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT593TA	AEC-Q101	FZT593	7	12	1,000

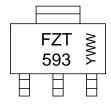
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**

Notes:

SOT223



FZT 593 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-100	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-1	Α
Base Current	I <sub>B</sub>	-200	mA
Peak Pulse Current	I <sub>CM</sub>	-2	А

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	D-	2.0	W	
Power Dissipation	(Note 7)	P <sub>D</sub>	1.6		
	(Note 8)		1.2	]	
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	D .	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	19.4		
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

## ESD Ratings (Note 10)

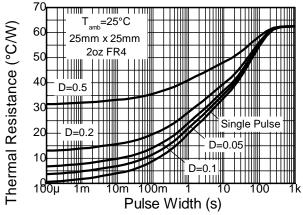
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

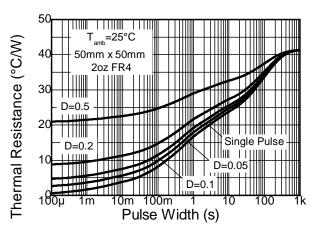
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



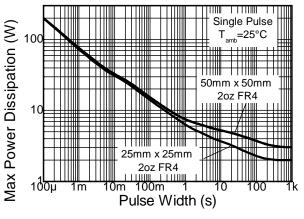
### **Thermal Characteristics and Derating Characteristics**



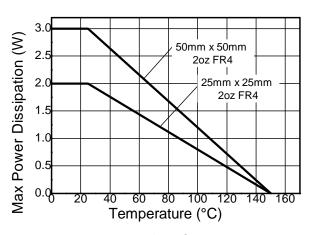
**Transient Thermal Impedance** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



**Derating Curve** 





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

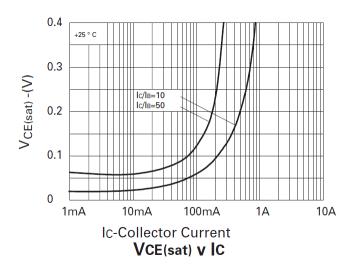
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-120	_	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	-100	_	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	_	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	-	_	-100	nA	V <sub>CB</sub> = -100V
Collector Cut-Off Current	I <sub>CES</sub>	-	_	-100	nA	V <sub>CE</sub> = -100V
Emitter Cut-Off Current	I <sub>EBO</sub>	-	_	-100	nA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage (Note 11)	V	_	_	-0.2	V	$I_C = -250 \text{mA}, I_B = -25 \text{mA}$
Collector-Emilier Saturation voltage (Note 11)	$V_{CE(sat)}$	-	_	-0.3		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	-	_	-1.1	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	_	-1.0	V	$I_C = -500 \text{mA}, V_{CE} = -5 \text{V}$
		100	_	-		$I_{C} = -1 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Gain (Note 11)	h	100	_	_		$I_C = -250 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Gain (Note 11)	h <sub>FE</sub>	100	_	300	_	$I_C = -500 \text{mA}, V_{CE} = -5 \text{V}$
		50	_	_		$I_C = -1A$ , $V_{CE} = -5V$
Current Gain-Bandwidth Product	f⊤	50	-	_	MHz	$V_{CE} = -10V, I_{C} = -50mA$
Ourient Gain Bandwidth Froduct	[]	30				f = 100MHz
Output Capacitance	$C_obo$	-	_	5	pF	$V_{CB} = -10V$ , $f = 1MHz$

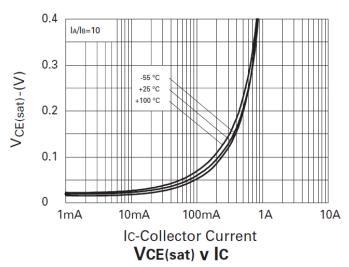
Note:

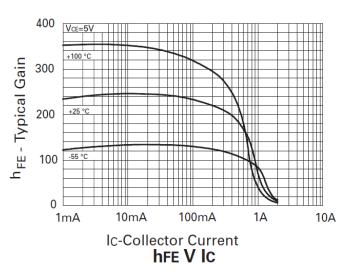
11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

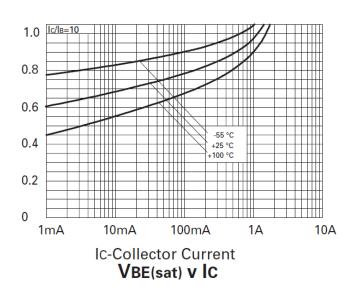


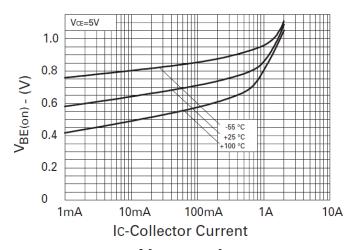
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)







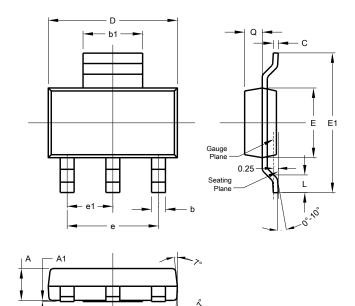






## **Package Outline Dimensions**

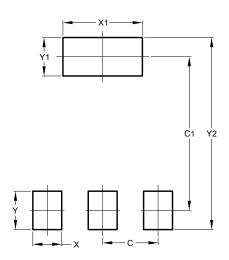
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Χ	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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